The charge asymmetry in superconductivity of hole- and electron-doped cuprates

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W ithin the $t+t^0-J$ model, the charge asymmetry in superconductivity of hole- and electron-doped cuprates is studied based on the kinetic energy driven superconducting mechanism. It is shown that superconductivity appears over a narrow range of doping in electron-doped cuprates, and the superconducting transition temperature displays the same kind of the doping controlled behavior that is observed in the hole-doped case. However, the maximum achievable superconducting transition temperature in electron-doped cuprates is much lower than that of the hole-doped case due to the electron-hole asymmetry.

74.20 M n, 74.62 D h, 74.25 D w

The parent com pounds of cuprate superconductors are believed to belong to a class of materials known as M ott insulators with the antiferrom agnetic (AF) long-range order (AFLRO), then superconductivity occurs by the electron or hole doping^{1{4}. Both hole-doped and electrondoped cuprate superconductors have the layered structure of the square lattice of the C uO 2 plane separated by insulating layers^{1;4}. It has been found from experiments that only an approximate symmetry in the phase diagram exists about the zero doping line between electronand hole-doped cuprates^{5;6}. For hole-doped cuprates^{1 $\{3\}$}, AFLRO disappears rapidly with doping, and is replaced by a disordered spin liquid phase, then the system s becom e superconducting (SC) over a wide range of the hole doping concentration , around the optimal 0:15, however, AFLRO survives until superconductivity appears over a narrow range of around the optimal

0:15 in electron-doped cuprates, where the maximum achievable SC transition temperature is much lower than hole-doped cuprates4;7;8. A lthough this electronhole asymmetry is observed in the phase diagram 1;5;6, the charge carrier Cooper pairs in the both optimally electron- and hole-doped cuprate superconductors have a dom instead d-wave symmetry 9^{12} . Since the strong electron correlation is common for both hole-doped and electron-doped cuprates, many of the physical properties of electron-doped cuprates resemble that of the holedoped case. By virtue of system atic studies using the nuclear magnetic resonance, and muon spin rotation techniques, particularly the inelastic neutron scattering, it has been well established that the AF short-range correlation in both hole-and electron-doped cuprate superconductors coexists with the SC state^{1;13 {15}. These provide a clear link between the charge carrier pairing mechanism and magnetic excitations, and show that both holeand electron-doped cuprate superconductors have sim ilar underlying SC mechanism 16 .

W ithin the t-J model, we^{17;18} have discussed the kinetic energy driven SC mechanism in hole-doped cuprates based on the charge-spin separation (CSS) ferm ion-spin theory¹⁹, where the dressed holons interact occurring directly through the kinetic energy by exchanging dressed spin excitations, leading to a net attractive force between dressed holons, then the electron Cooper

pairs originating from the dressed holon pairing state are due to the charge-spin recombination, and their condensation reveals the SC ground-state¹⁷. The SC transition tem perature is controlled by both charge carrier gap function and single particle coherent weight. This single particle coherent weight grows linearly with increasing doping in the underdoped and optim ally doped regimes, and then decreases with increasing doping in the overdoped regime, which leads to that the maxim alsuperconducting transition temperature occurs around the optim aldoping, and then decreases in both underdoped and overdoped requires e^{18} . In this paper, we study the charge asymmetry in superconductivity of hole- and electrondoped cuprates along with this line. We show that superconductivity appears over a narrow range of doping in electron-doped cuprates, and the maximum achievable SC transition tem perature in the optim aldoping is lower than that of the hole-doped case due to the electron-hole asym m etry.

In both hole- and electron-doped cuprates, the characteristic feature is the presence of the two-dimensional $C uO_2 plane^{1;4}$ as mentioned above, and it seems evident that the unusual behaviors are dom inated by this plane. A lthough the t-J m odel captures the essential physics of the doped $C uO_2 plane^{20}$, the electron-hole asym metry m ay be accounted for by including further neighbor hoping t^{021} . Therefore we start from the t-t⁰-J m odel,

$$H = t C_{i}^{Y} C_{i+} + t^{0} C_{i}^{Y} C_{i+} + t^{0} C_{i}^{Y} C_{i+} + C_{i}^{Y} C_{i+} + J C_{i+}^{Y} C_{i+$$

with ^ = \Re ; \Re , ^ = \Re \Re , C_i^y (C_i) is the electron creation (annihilation) operator, $S_i = C_i^y \sim C_i = 2$ is spin operator with ~ = ($_x$; $_y$; $_z$) as Paulim atrices, and is the chemical potential. For the electron doping, we can perform a particle-hole transformation C_i ! C_i^y , so that the di erence between hole and electron doping is expressed as the sign di erence of the hopping param – eters, i.e., t> 0 and t⁰ > 0 for hole doping and t < 0 and t⁰ < 0 for electron doping²², then the t-t⁰-J m odel (1) in both hole- and electron-doped cases is always subject to an important on-site local constraint to avoid the double

occupancy, i.e., $P C_i^y C_i$ 1. This single occupancy local constraint can be treated properly within the CSS ferm ion-spin theory¹⁹, where the constrained electron operators are decoupled as, $C_{i^*} = h_{i^*}^y S_i$, $C_{i^\#} = h_{i^\#}^y S_i^+$, with the spinful ferm ion operator $h_i = e^{i \cdot i} h_i$ describes the charge degree of freedom together with some e ects of the spin con guration rearrangements due to the presence of the doped charge carrier itself (dressed charge carrier), while the spin operator S_i describes the spin degree of freedom (dressed spin), then the electron local constraint for the single occupancy is satis ed in analytical calculations, and low-energy behavior of the t+t^0-J m odel (1) in this CSS ferm ion-spin representation can be expressed as^{17{19}}.

$$H = t \begin{pmatrix} X \\ h_{i''}S_{i}^{+}h_{i+\wedge ''}^{Y}S_{i+\wedge} + h_{i\#}S_{i}h_{i+\wedge \#}^{Y}S_{i+\wedge}^{+} \end{pmatrix} + t^{0} \begin{pmatrix} A_{i''}S_{i}^{+}h_{i+\wedge "}^{Y}S_{i+\wedge} + h_{i\#}S_{i}h_{i+\wedge \#}^{Y}S_{i+\wedge}^{+} \end{pmatrix} \\ X \begin{pmatrix} A_{i''}S_{i}^{+}h_{i+\wedge "}^{Y}S_{i+\wedge} + h_{i\#}S_{i}h_{i+\wedge \#}^{Y}S_{i+\wedge}^{+} \end{pmatrix} \\ X \begin{pmatrix} A_{i''}S_{i}^{+}h_{i+\wedge "}^{Y}S_{i+\wedge} + h_{i\#}S_{i}h_{i+\wedge \#}^{Y}S_{i+\wedge}^{+} \end{pmatrix} \\ X \begin{pmatrix} A_{i''}S_{i}^{+}h_{i+\wedge "}^{Y}S_{i+\wedge} + h_{i\#}S_{i}h_{i+\wedge \#}^{Y}S_{i+\wedge}^{+} \end{pmatrix} \\ X \begin{pmatrix} A_{i''}S_{i}^{+}h_{i+\wedge "}^{Y}S_{i+\wedge} + h_{i\#}S_{i}h_{i+\wedge \#}^{Y}S_{i+\wedge}^{+} \end{pmatrix} \\ X \begin{pmatrix} A_{i''}S_{i+\wedge "}^{+}h_{i+\wedge "}S_{i+\wedge "} + h_{i\#}S_{i+\wedge \#}^{Y}S_{i+\wedge \#}^{+} \end{pmatrix} \\ X \begin{pmatrix} A_{i''}S_{i+\wedge "}S_{i+\wedge "}S_{i+\wedge "} + h_{i\#}S_{i}h_{i+\wedge \#}^{Y}S_{i+\wedge \#}^{+} \end{pmatrix} \\ X \begin{pmatrix} A_{i''}S_{i+\wedge "}S_{i+\wedge "}S_{i+\wedge "} + h_{i\#}S_{i+\wedge \#}^{Y}S_{i+\wedge \#}^{+} \end{pmatrix} \\ X \begin{pmatrix} A_{i''}S_{i+\wedge "}S_{i+\wedge "}S_{i+\wedge "}S_{i+\wedge \#} + h_{i\#}S_{i+\wedge \#}^{Y}S_{i+\wedge \#}^{+} \end{pmatrix} \\ X \begin{pmatrix} A_{i''}S_{i+\wedge "}S_{i+\wedge "}S_{i+\wedge "}S_{i+\wedge \#} + h_{i\#}S_{i+\wedge \#}^{Y}S_{i+\wedge \#}^{+} \end{pmatrix} \end{pmatrix}$$

with $J_e = (1 \ x)^2 J$, and $= h_1^y h_i i = h_1^y h_i i$ is the doping concentration. As a consequence, the kinetic energy terms in the t-t⁰-J m odelhave been expressed as the interactions between dressed charge carriers and spins, which re exts that even the kinetic energy terms in the t-t⁰-J H am iltonian have strong C oulom bic contributions due to the restriction of no doubly occupancy of a given site. These interactions between dressed charge carriers and spins are quite strong, and w e^{17;18} have shown that in the case without AFLRO, these interactions can induce the dressed charge carrier pairing state (then the electron C ooper pairing state) by exchanging dressed spin excitations in the higher power of the doping concentration

. Since the SC state in both hole- and electron-doped cuprates is characterized by the electron C ooper pairs, form ing SC quasiparticles^{9;12}, and in the real space the gap function and pairing force have a range of one lattice spacing²³, therefore the order param eter for the electron C ooper pair can be expressed as, $= hC_{ir}^{y}C_{i+\uparrow}^{y}$, $C_{i\#}^{y}C_{i+\uparrow}^{y}$, $C_{i\#}^{y}C_{i+\uparrow}^{y}$, $h_{i\#}h_{i+\uparrow}^{x}S_{i}^{+}S_{i+\uparrow}$, $h_{i\#}h_{i+\uparrow}rS_{i}S_{i+\uparrow}^{y}$, $C_{i\#}^{y}C_{i+\uparrow}^{y}$, $h_{i\#}h_{i+\uparrow}rS_{i}S_{i+\uparrow}$, $h_{i\#}h_{i+\uparrow}rS_{i}S_{i+\uparrow}$, $h_{i\#}h_{i+\uparrow}rS_{i}S_{i+\uparrow}$, $h_{i\#}h_{i+\uparrow}rS_{i}S_{i+\uparrow}$, $h_{i\#}h_{i+\uparrow}rS_{i}S_{i+\uparrow}$, $h_{i\#}h_{i+\uparrow}rS_{i+\uparrow}$, h_{i} , which shows that the SC order param eter is closely related to the dressed charge carrier pairing am plitude, and is proportional to the num ber of charge carriers, and not to the num ber of electrons. Follow ing the E liashberg's strong coupling theory²⁴, we obtain the self-consistent equations that satis ed by the full dressed charge carrier diagonal

and o -diagonal G reen's functions as¹⁷,

$$g(k) = g^{(0)}(k) + g^{(0)}(k) \begin{bmatrix} {h \choose 1} & k \end{pmatrix} g(k)$$
$${}^{(h)}_{2}(k) = {}^{y}(k)]; \qquad (3a)$$
$$= {}^{y}(k) = g^{(0)}(k) \begin{bmatrix} {h \choose 1} & k \end{pmatrix} = {}^{y}(k)$$

$$+ \frac{(h)}{2}(k)g(k)];$$
 (3b)

respectively, where the four-vector notation $k = (k;i!_n)$, the dressed charge carrier mean-eld (MF) diagonal G reen's function 17 g $^{(0)\ 1}$ (k) = i!_n k, the MF dressed charge carrier excitation spectrum $_k$ = Zt $_1$ $_{\dot{B}}$ Zt 0_2 0_k , with $_k$ = (1=Z) $_{\dot{A}}e^{ik}$, 0_k = (1=Z) $_{\dot{A}}e^{ik}$, 2_k is the number of the nearest neighbor or second-nearest neighbour sites, the dressed spin correlation functions $_1$ = hS_i^+S_{i+}^-i and $_2$ = hS_i^+S_{i+}^-i, and the dressed charge carrier self-energy functions $^{17;18}$,

ip_m⁰

where $p = (p; ip_m), p^0 = (p^0; ip_m^0)$, and the MF dressed spin G reen's function¹⁷,

ipm

$$D^{(0)}(p) = \frac{B_{p}}{(ip_{m})^{2} ! p_{p}^{2}};$$
(5)

with $B_p = {}_1[2 {}_1^{z}(p {}_1) + {}_1(p {}_1)] {}_2(2 {}_2^{z} {}_0^{0}) {}_2), {}_1 = 2Z J_{eff}, {}_2 = 4Z {}_2t^{0}, {}_1 = 1 + 2t {}_1=J_{e}, {}_1$ and the MF dressed spin excitation spectrum $!_p^2 = A_1({}_k)^2 + A_2({}_k)^2 + A_3 {}_k {}_k^0 + A_4 {}_k + A_5 {}_k^0 + A_6, {}_1$ with $A_1 = {}_1^2({}_1^{z} + {}_1=2), A_2 = {}_2^2{}_2^{z}, A_3 = {}_1{}_2({}_1^{z} + {}_2^{z} + {}_1=2), A_4 = {}_1^2[({}_1^{z} + {}_1=2) + (C_1^z + (1 {})=(4Z) {}_1=(2Z)) + (C_1 + (1 {})=(4Z) {}_1=(2Z)) + (C_1 + (1 {})=(4Z) {}_1=(2Z) + {}_1{}_2({}_1^{z} + {}_1=2+C_3^z), A_6 = {}_1^2[C_1^z + (1 {})=(4Z) {}_1=(2Z) + {}_1{}_2(C_1 + (1 {})=(2Z) {}_1=(2Z) {}_1=(2Z) + {}_2{}_2(C_2 + (1 {})=(2Z) {}_2=2)=2)$

 $^{1}_{1}$ $_{2}C_{3}$, and the dressed charge carrier's particlehole parameters $_{1}$ = $hh_{i}^{y}h_{i+} \wedge i$, $_{2}$ = $hh_{i}^{y}h_{i+} \wedge i$, the dressed spin correlation functions $_{1}^{z}$ = $hS_{i}^{z}S_{i+}^{z} \wedge i$, $_{2}^{z}$ = $hS_{i}^{z}S_{i+}^{z} \wedge i$, C_{1} = $(1=Z^{2})^{P}$ $_{\gamma} \wedge hS_{i+}^{z} \wedge S_{i+} \wedge i$, C_{1}^{z} = $(1=Z^{2})^{P}$ $_{\gamma} \wedge hS_{i+}^{z} \wedge S_{i+} \wedge i$, C_{1}^{z} = $(1=Z^{2})^{P}$ $_{\gamma} \wedge hS_{i+}^{z} \wedge S_{i+} \wedge i$, and C_{3}^{z} = $(1=Z)^{P}$ $_{\Lambda}hS_{i+}^{z} \wedge S_{i+}^{z} \wedge i$. In order to satisfy the sum rule of the correlation function $hS_{i}^{+}S_{i}$ i = 1=2 in the case without AFLRO, the important decoupling parameter has been introduced in the MF calculation^{17}, which can be regarded as the vertex correction.

In Eq. (4), the self-energy function $\binom{(h)}{2}(k)$ is called as the electrice dressed charge carrier gap function since it contains both pairing force and dressed charge carrier gap function, while the self-energy function $\binom{(h)}{1}(k)$ renorm alizes the M F dressed charge carrier spectrum, and there-

fore it describes the single particle (quasiparticle) coherence. In particular, ${2 \choose 2}$ (k) is an even function of i! , while $\begin{pmatrix} h \\ 1 \end{pmatrix}$ (k) is not. For the convenience of discussions, we separate $\binom{(h)}{1}$ (k) into its symmetric and antisymmet- $\operatorname{ric} \operatorname{parts} \operatorname{as}, \begin{array}{c} \stackrel{(h)}{1} (k) = \begin{array}{c} \stackrel{(h)}{1e} (k) + i!_{n} \begin{array}{c} \stackrel{(h)}{1o} (k), \text{ then } \begin{array}{c} \stackrel{(h)}{1e} (k) \end{array}$ and $\binom{(h)}{10}$ (k) are both even functions of i! n . A coording to the E liashberg's strong coupling theory²⁴, we can de ne the charge carrier single particle (quasiparticle) coherent weight $Z_F^{(1)}(k) = 1$ $\binom{(h)}{10}(k)$. On the other hand, the retarded function Re $\binom{(h)}{1e}(k)$ may be a constant, independent of $(k \cdot 1)$. This is the retarded function $R = \binom{(h)}{1e}(k)$ may be a constant, independent of $(k \cdot 1)$. dent of (k;!). It just renorm alizes the chem ical potential, and therefore can be neglected²⁴. Furtherm ore, we only study the static lim it of the e ective dressed charge carrier gap function and single particle coherent weight, i.e., ${}_{2}^{(h)}(k) = {}_{h}(k)$, and $Z_{F}^{(1)}(k) = 1$ ^(h) (k). A 🗠 though $Z_F(k)$ still is a function of k, the wave vector dependence is unim portant, since everything happens at the electron Ferm i surface. As in the previous discussions within the t-J model¹⁸, the special wave vector can be estim ated qualitatively from the electron m om entum distribution as $k_0 = k_A - k_F$ with $k_A = [;]$ [(1 x) = 2; (1 x) = 2], which guarantees and $k_{\rm F}$ $Z_F = Z_F (k_0)$ near the electron Ferm i surface. In this case, the dressed charge carrier diagonal and o -diagonal G reen's functions in Eq. (3) can be rewritten explicitly as,

$$g(k) = \frac{1}{2} + \frac{1}{E_{k}} + \frac{Z_{F}}{i!_{n} E_{k}} + \frac{1}{2} + \frac{1}{E_{k}} + \frac{1}{E_{k}} + \frac{Z_{F}}{i!_{n} + E_{k}}; \qquad (6a)$$

$$={}^{Y}(k) = \frac{1}{2} \frac{{}_{hZ}(k)}{{}_{E}_{k}} \frac{{}_{Z}_{F}}{{}_{i!}_{n} {}_{E}_{k}} \frac{{}_{Z}_{F}}{{}_{i!}_{n} {}_{E}_{k}} \frac{{}_{Z}_{F}}{{}_{i!}_{n} {}_{E}_{k}} ; (6b)$$

with $_{k} = Z_{F \ k}$, $_{hZ}$ (k) = $Z_{F \ h}$ (k), and the <u>dressed charge carrier</u> quasiparticle spectrum $E_{k} =$

 $_{k}^{2}$ + j $_{hZ}$ (k) f.

A lthough superconductivity with both d-wave and swave symmetries appear within the t-J model, the SC state has a dominated d-wave symmetry in the optimal doping¹⁸. Moreover, we²⁵ have discussed the e ect of the additional second neighbor hopping t⁰ on superconductivity, and found that the d-wave SC pairing correlation is enhanced, while the s-wave SC pairing correlation is heavily suppressed. In this paper, we are interested in the charge asymmetry in superconductivity of hole- and electron-doped cuprates. To make the discussions simpler, we only consider the d-wave case, i.e., $_{hZ}(k) = _{hZ} _{k}^{(d)}$, with $_{k}^{(d)} = (\cos k_x - \cos k_y)=2$. In this case, the dressed charge carrier elective gap param – eter and single particle coherent weight in Eq. (4) satisfy the following equations^{17;18},

$$1 = \frac{1}{N^{3}} \sum_{k \neq q, p}^{X} (Z t_{k+q} - Z t^{0} \frac{0}{k+q})^{2} \frac{(d)}{k p+q} \sum_{k}^{(d)} \frac{Z_{F}^{2}}{E_{k}} \frac{B_{q} B_{p}}{!_{q} !_{p}}$$

$$\frac{F_{1}^{(1)}(k;q;p)}{(!_{p} !_{q})^{2} E_{k}^{2}} + \frac{F_{1}^{(2)}(k;q;p)}{(!_{p} + !_{q})^{2} E_{k}^{2}}; \quad (7a)$$

$$Z_{F} = 1 + \frac{1}{N^{2}} X_{q;p} (Z t_{p+k_{0}} Z t_{p+k_{0}}^{0})^{2} Z_{F} \frac{B_{q}B_{p}}{4!_{q}!_{p}}$$

$$- \frac{F_{2}^{(1)}(q;p)}{(!_{p} !_{q} E_{p}q+k_{0})^{2}} + \frac{F_{2}^{(2)}(q;p)}{(!_{p} !_{q} + E_{p}q+k_{0})^{2}}$$

$$+ \frac{F_{2}^{(3)}(q;p)}{(!_{p} + !_{q} E_{p}q+k_{0})^{2}} + \frac{F_{2}^{(4)}(q;p)}{(!_{p} + !_{q} + E_{p}q+k_{0})^{2}}; \quad (7b)$$

respectively,

1

where $F_1^{(1)}(k;q;p) = (!_p !_q) [n_B (!_q) n_B (!_p)] [1$ $2n_F (E_k)] + E_k [n_B (!_p)n_B (!_q) + n_B (!_q)n_B (!_p)],$ $F_1^{(2)}(k;q;p) = (!_p + !_q) [n_B (!_q) n_B (!_p)] [1$ $2n_F (E_k)] + E_k [n_B (!_p)n_B (!_q) + n_B (!_p)n_B (!_q)],$ $F_2^{(1)}(q;p) = n_F (E_{p q+k_0}) [n_B (!_q) n_B (!_p)]$ $n_B (!_p)n_B (!_q), F_2^{(2)}(q;p) = n_F (E_{p q+k_0}) [n_B (!_p)]$ $n_B (!_q)] n_B (!_q), F_2^{(2)}(q;p) = n_F (E_{p q+k_0}) [n_B (!_p)] +$ $n_B (!_p)n_B (!_q), F_2^{(4)}(q;p) = n_F (E_{p q+k_0}) [n_B (!_p)] +$ $n_B (!_p)n_B (!_q), F_2^{(4)}(q;p) = n_F (E_{p q+k_0}) [n_B (!_p)] +$ $n_B (!_p)] + n_B (!_p)n_B (!_q), and n_B (!) and n_F (!) are the boson and ferm ion distribution functions, respectively. These two equations must be solved simultaneously with other self-consistent equations^{17;18},$

$$= \frac{1}{2N} \sum_{k}^{X} 1 \frac{k}{E_{k}} th [\frac{1}{2} E_{k}] ; \qquad (8a)$$

$$P_{2} = \frac{1}{2N} \sum_{k}^{X} 0 = \frac{1}{E_{k}} \ln \left[\frac{1}{2} E_{k}\right] ; \qquad (8b)$$

$$= \frac{1}{2N} \sum_{k}^{X} 1 \frac{k}{E_{k}} th [\frac{1}{2} E_{k}] ; \qquad (8c)$$

$$_{1} = \frac{1}{N} \sum_{k}^{K} \frac{B_{k}}{2!_{k}} \operatorname{octh}[\frac{1}{2} !_{k}]; \qquad (8d)$$

$${}_{2} = \frac{1}{N} \sum_{k}^{N} \frac{{}_{0} \frac{B_{k}}{2!_{k}}} \operatorname{oth} [\frac{1}{2} !_{k}]; \qquad (8e)$$

$$C_{1} = \frac{1}{N} \sum_{k}^{X} \frac{{}_{k}^{2} B_{k}}{2!_{k}} \operatorname{coth} [\frac{1}{2} !_{k}]; \qquad (8f)$$

$$C_{2} = \frac{1}{N} \sum_{k}^{N} \frac{\alpha_{k}}{k} \frac{B_{k}}{2!_{k}} \operatorname{coth}[\frac{1}{2} !_{k}]; \qquad (8g)$$

$$C_{3} = \frac{1}{N} \sum_{k}^{X} \sum_{k=0}^{k} \frac{B_{k}}{2!_{k}} \operatorname{oth} [\frac{1}{2} !_{k}]; \qquad (8h)$$

$$\frac{1}{2} = \frac{1}{N} \sum_{k}^{X} \frac{B_{k}}{2!_{k}} \operatorname{oth} [\frac{1}{2} !_{k}]; \qquad (8i)$$

$${}_{1}^{z} = \frac{1}{N} {}_{k}^{X} {}_{k} \frac{B_{z}(k)}{2!_{z}(k)} \operatorname{oth} [\frac{1}{2} !_{z}(k)]; \qquad (8)$$

$${}_{2}^{z} = \frac{1}{N} {}_{k}^{X} {}_{k}^{0} \frac{B_{z}(k)}{2!_{z}(k)} \operatorname{oth} [\frac{1}{2} !_{z}(k)]; \qquad (8k)$$

$$C_{1}^{z} = \frac{1}{N} \sum_{k}^{X} \frac{2}{2! z(k)} \operatorname{coth} [\frac{1}{2} ! z(k)]; \qquad (81)$$

$$C_{3}^{z} = \frac{1}{N} \frac{X}{k} + \frac{0}{k} \frac{B_{z}(k)}{2!_{z}(k)} \operatorname{coth} [\frac{1}{2} !_{z}(k)]; \quad (8m)$$

then all the above order param eters, decoupling param – eter , and chem ical potential are determ ined by the self-consistent calculation 17,18 .

It has been show n^{17} that the dressed charge carrier pairing state originating from the kinetic energy term s by exchanging dressed spin excitations can lead to form the electron C ooper pairing state, where the SC gap function is obtained from the electron o -diagonal G reen's function ^y(i j;t t⁰) = $hC_{j^{*}}^{y}(t);C_{j^{\#}}^{y}(t^{0})$ ii, which is a convolution of the dressed spin G reen's function and dressed charge carrier o -diagonal G reen's function, and re ects the charge-spin recom bination²⁶. In the present case, this electron o -diagonal G reen's function can be obtained in term s of the M F dressed spin G reen's function (5) and dressed charge carrier o -diagonal G reen's function (6b) as,

$${}^{y}(k) = \frac{1}{N} \sum_{p}^{X} \frac{Z_{F \ hZ}(p \ k)}{E_{p \ k}} \frac{B_{p}}{2!_{p}}$$

$$\frac{(!_{p} + E_{p \ k})[h_{B}(!_{p}) + n_{F}(E_{p \ k})]}{(i!_{n})^{2} \ (!_{p} + E_{p \ k})^{2}}$$

$$\frac{(!_{p} \ E_{p \ k})[h_{B}(!_{p}) + n_{F}(E_{p \ k})]}{(i!_{n})^{2} \ (!_{p} \ E_{p \ k})^{2}} ; (9)$$

W ith the help of this electron o -diagonal G reen's function, the SC gap function is obtained as $(k) = (1 =)_{j_1} = {}^{y}(k; i!_n)$, and can be evaluated explicitly,

$$(k) = \frac{1}{N} \frac{X}{p} \frac{Z_{F \ hZ}(p \ k)}{2E_{p \ k}} \\ tanh[\frac{1}{2} \ E_{p \ k}] \frac{B_{p}}{2!_{p}} \operatorname{coth}[\frac{1}{2} \ !_{p}]; \qquad (10)$$

which shows that the SC transition temperature $T_{\rm c}$ occurring in the case of the SC gap parameter = 0 is identical to the dressed charge carrier pair transition tem perature occurring in the case of the e ective dressed charge carrier pairing gap parameter $h_{\rm Z} = 0$. Since the absolute values of t and t⁰ are alm ost sam e for both hole-and electron-doped cuprates²¹, and therefore in this paper, the commonly used parameters are chosen as t=J = 25and $t^0 = t = 0.3$ for the hole doping, and t = J = 0.32:5 and t⁰=t = 0:3 for the electron doping. In Fig. 1, we plot the SC transition temperature $T_{\rm c}$ as a function of the doping concentration for (a) the electron doping and (b) the hole doping in comparison with the corresponding experimental results of Pr $_2$ x Ce_xCuO $_4$ y 8 and $La_{2x} Sr_{x}CuO_{4}^{3}$ (inset). Our results indicate that for the hole-doped case, superconductivity appears over a wide range of doping, where the maxim alSC transition tem perature T_c occurs around the optim aldoping concentration opt 0:15, and then decreases in both underdoped

and overdoped regimes. In analogy to the phase diagram of the hole-doped case, superconductivity appears over a narrow range of doping in the electron-doped side, where the SC transition temperature T_c increases sharply with increasing doping in the underdoped regime, and reaches a maximum in the optimal doping opt 0:14, then decreases sharply with increasing doping in the overdoped regime. However, the maximum achievable SC transition tem perature in the optim aldoping in electron-doped cuprates is much lower than that of the hole-doped case due to the electron-hole asymmetry. Using an reasonably estimative value of J 800K to 1200K in doped cuprates, the SC transition temperature in the optimal doping is T_c 022J 176K 264K for the holedoped case, and T_c 0:136J 108K 163K for the electron-doped case, in qualitative agreem ent with the corresponding experim ental data 3;4;8.

The essential physics of the doping dependent SC transition temperature in the electron-doped case is almost the same as in the hole-doped side, and detailed explanations have been given in Ref. [18]. In the framework of the kinetic energy driven superconductivity¹⁷, the self-energy function $\binom{(h)}{2}(k)$ describes the elective dressed charge carrier pairing gap function, and measures the strength of the binding of charge carrier pairs, while the antisymmetric part of the self-energy function

 ${}_{1o}^{(h)}$ (k) (then Z_F) describes the single particle (quasiparticle) coherence, and therefore Z_F is closely related to the quasiparticle density. Since the SC state is established through an emerging quasiparticle²⁷, then the SC state is controlled by both gap function and quasiparticle coherence, which is relected explicitly in the selfconsistent equations (7a) and (7b). It has been shown that the doping dependent behavior of the single particle coherent weight resembles that of the super uid density in doped cuprates¹⁸, i.e., Z_F grows linearly with the doping concentration in the underdoped and optim ally doped regim es, and then decreases with increasing doping in the overdoped regim e, which leads to that the SC transition tem perature reaches a maximum in the optim al doping,

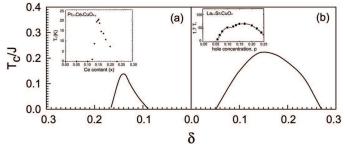


FIG.1. The superconducting transition temperature as a function of the doping concentration with (a) t=J = 2.5 and t^0 =t = 0.3 for the electron doping and (b) t=J = 2.5 and t^0 =t = 0.3 for the hole doping. Inset: the corresponding experimental results of Pr₂ xCe_xCuO₄ y taken from Ref. [8] and La₂ xSr_xCuO₄ from Ref. [3].

and then decreases in both underdoped and overdoped regimes. On the other hand, it has been show n^{21} that AFLRO can be stabilized by the t^0 term for the electron-doped case, which m ay lead to the charge carrier's localization over a broader range of doping, this is also why superconductivity appears over a narrow range of doping in electron-doped cuprates.

In the CSS ferm ion-spin theory¹⁹, the physical electron is decoupled as the dressed charge carrier $h_i = e^{i} h_i$ and spin S_i . Since the phase factor i in the dressed charge carrier is separated from the bare spinon operator, and then it describes a spin cloud¹⁹. Therefore the dressed charge carrier h_i is a spinless ferm ion h_i (bare charge carrier) incorporated the spin cloud e i (magnetic ux), thus is a magnetic dressing. In other words, the dressed charge carrier carries som e spin m essages, i.e., it shares its nontrivial spin environment. It has been show n¹⁹ that these dressed charge carrier and spin are gauge invariant under a local U (1) gauge transform ation, and in this sense, they are real and can be interpreted as the physical excitations. In doped cuprates, the norm al-state above the SC transition temperature exhibits a number of anom alous properties which is due to CSS²⁰, while the SC state is characterized by the charge-spin recombination²⁶. Based on the CSS ferm ionspin theory, we²⁸ have discussed the charge dynam ics of the underdoped cuprates in the norm al-state, and show that under tem perature T , the magnetic uctuation is strong enough to lead to a pseudogap. This pseudogap would reduce the charge carrier scattering and thus is responsible for the tem perature linear to the nonlinear range in the in-plane resistivity and the crossovers to the insulating-like range in the c-axis resistivity. Furtherm ore, the tem perature T is doping dependent, and grows monotonously as the doping concentration decreases, and disappear in higher doping²⁸. It has been show n^{28} that this pseudogap (then the tem perature T) is obtained from the charge carrier G reen's function in the norm al-state by considering the second-order correction due to the spin pair bubble. In the kinetic energy driven SC m echanism 17;18, the charge carrier pairing state (then the electron SC-state and SC transition tem perature T_c) occurrs directly through the kinetic energy by exchanging spin excitations, and is controlled by both charge carrier gap function and single particle coherent weight. This single particle coherent weight is obtained from the charge carrier quasiparticle diagonalG reen's function in the SC-state by considering the second-order correction due to the spin pair bubble, and at the sam e tim e is e ected by the dressed charge carrier pair gap function (then the charge carrier quasiparticle o -diagonal G reen's function), which is shown explicitly in the self-consistent equations (7a) and (7b). M oreover, this dressed charge carrier pairing amplitude (then the SC order parameter) is proportional to the number of charge carrier quasiparticles (then the super uid density), and not to the number of electrons as mentioned above, which leads to¹⁸ that the single particle coherent weight Z_F (T_c) resembles that of the super uid density. In other words, T is closely related to the spin uctuation, while T_c is self-consistently governed by the single particle coherence and dressed charge carrier pair gap function, this is why there are some di erences between T and T_c .

In summary, within the framework of the kinetic energy driven the SC mechanism¹⁷, we have discussed the charge asymmetry in superconductivity of hole-and electron-doped cuprates based on the t-t⁰-J m odel. Our results show that for the hole-doped case, superconductivity appears over a wide range of doping, where the maximal SC transition temperature occurs around the optim al doping concentration, and then decreases in both underdoped and overdoped regimes. In analogy to the phase diagram of hole-doped case, superconductivity appears over a narrow range of doping in the electron-doped side, where the SC transition temperature increases sharply with increasing doping in the underdoped regime, and reaches a maximum in the optimal doping, then decreases sharply with increasing doping in the overdoped regime. However, the maximum achievable SC transition temperature in the optim aldoping in the electron-doped case is much lower than that of the hole-doped side due to the electron-hole asym m etry. O ur these results are in qualitative agreem ent with the experim ental observations.

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